TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRIAC

TLP3020,TLP3021,TLP3022,TLP3023

OFFICE MACHINE HOUSEHOLD USE EQUIPMENT TRIAC DRIVER SOLID STATE RELAY

The TOSHIBA TLP3020, TLP3021, TLP3022 and TLP3023 consist of a photo-triac optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package.

: 400 V (Min.) • Peak Off-State Voltage

Trigger LED Current : 30mA (Max.) (TLP3020)

> 15 mA (Max.) (TLP3021) 10 mA (Max.) (TLP3022) 5 mA (Max.) (TLP3023)

On-State Current : 100 mA (Max.)

UL Recognized : UL1577, File No. E67349

Isolation Voltage : 5000 Vrms (Min.)

Option (D4) Type

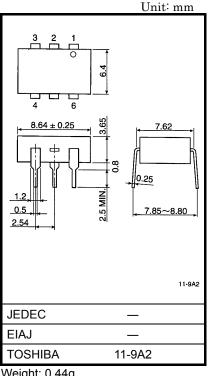
 VDE Approved : DIN EN 60747-5-2, Certificate No. 40009302

Maximum Operating Insulation Voltage: 630 VPK Highest Permissible Over Voltage: 6000 VPK

Note: When a EN 60747-5-2 approved type is needed, please designate the "Option (D4)"

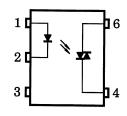
7.62mm pich

			standard type	(LF2) type
•	Creepage Distance	: -	7.0 mm (Min.)	8.0 mm (Min.)
	Clearance	:	7.0 mm (Min.)	8.0 mm (Min.)
	Insulation Thickness	:	0.5 mm (Min.)	0.5 mm (Min.)



Weight: 0.44g

PIN CONFIGURATION (TOP VIEW)



ANODE

CATHODE

3: N.C.

4: TERMINAL 1

6: TERMINAL 2

10.16 mm pich



Absolute Maximum Ratings (Ta=25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT		
	Forward Current		I _F	50	mA	
	Forward Current Derating (Ta ≥ 53°C)		ΔI _F /°C	-0.7	mA/°C	
	Peak Forward Current (100μs pulse, 100pps)		l _{FP}	1	А	
LED	Power Dissipation		P_{D}	100	mW	
	Power Dissipation Derating (Ta ≥ 25°C)		∆P _D /°C	-1.0	mW/°C	
	Reverse Voltage		V_{R}	5	V	
	Junction Temperature		Tj	125	°C	
	Off-State Output 1	erminal Voltage	V_{DRM}	400	V	
	On-Stage RMS	Ta=25°C	IT(DMO)	100	mA	
	Current	Ta=70°C	I _{T(RMS)}	50	IIIA	
œ	On-State Current Derating (Ta ≥ 25°C)		ΔI _T /°C	-1.1	mA/°C	
DETECTOR	Peak On-Stage Current (100 µs pulse, 120pps)		l _{TP}	2	А	
DET	Peak Nonrepetitive Surge Current (P _W =10ms, DC=10%)		I _{TSM}	1.2	А	
	Power Dissipation		P _D	300	mW	
	Power Dissipation Derating (Ta ≥ 25°C)		ΔP _D /°C	-4.0	mW/°C	
	Junction Temperature		Tj	115	°C	
Storage Temperature Range		T _{stg}	− 55 ~ 150	°C		
Operating Temperature Range			T _{opr}	− 40 ~ 100	°C	
Lead Soldering Temperature (10s)			T _{sol}	260	°C	
Total Package Power Dissipation			PT	330	mW	
Total Package Power Dissipation Derating (Ta ≥ 25°C)			ΔP _T /°C	-4.4	mW/°C	
	ion Voltage 1 min., R.H. ≤ 60%)	(Note 1)	BVS	5000	Vrms	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Device considered a two terminal device: Pins 1, 2 and 3 shorted together and pins 4 and 6 shorted together.



Recommended Operating Conditions

CHARACTERISTICS	SYMBOL	MIN	TYP.	MAX	UNIT
Supply Voltage	V_{AC}	_	_	120	Vac
Forward Current	l _F *	15	20	25	mA
Peak On-Stage Current	I _{TP}	_	_	1	А
Operating Temperature	T _{opr}	-25		85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

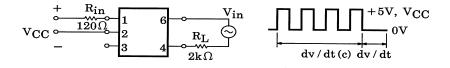
Individual Electrical Characteristics (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
	Forward Voltage	V _F	I _F =10mA	1.0	1.15	1.3	V
LED	Reverse Current	I _R	V _R =5V	_	_	10	μА
	Capacitance	C _T	V=0, f=1MHz	_	10	_	pF
~	Peak Off-State Current	I _{DRM}	V _{DRM} =400V	_	10	100	nA
	Peak On-Stage Voltage	V _{TM}	I _{TM} =100mA	_	1.7	3.0	V
CTO	Holding Current	lΗ	_	_	0.6	_	mA
DETECTOR	Critical Rate of Rise of Off- State Voltage	dv / dt	V _{in} =120Vrms, Ta=85°C (Fig.1)	200	500	_	V/μs
	Critical Rate of Rise of Commutating Voltage	dv / dt(c)	V _{in} =30Vrms, IF=15mA (Fig.1)	_	0.2	_	V/μs

Coupled Electrical Characteristics (Ta=25°C)

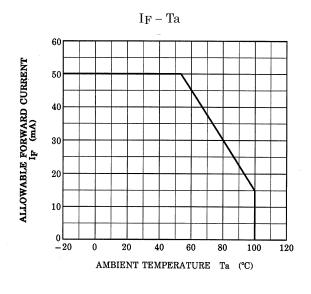
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT	
	TLP3020	let	V _T =3V	_	_	30	mA	
Trigger LED Current	TLP3021			_	_	15		
Trigger LLD Current	TLP3022			_	5	10		
	TLP3023			_	_	5		
Capacitance Input to Output		CS	V _S =0, f=1MHz	_	0.8	_	pF	
Isolation Resistance		R _S	V _S =500V (R.H. ≤ 60%)	5×10 ¹⁰	10 ¹⁴	_	Ω	
Isolation Voltage			AC, 1 minute		_	_	V _{rms}	
		B _{VS}	AC, 1 second (in oil)	_	10000	_		
			DC, 1 minute (in oil)	_	10000		V _{dc}	

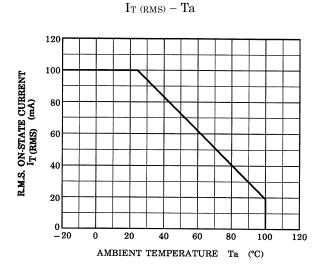
Fig. 1 dv/dt TEST CIRCUIT

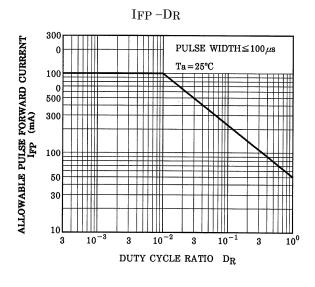


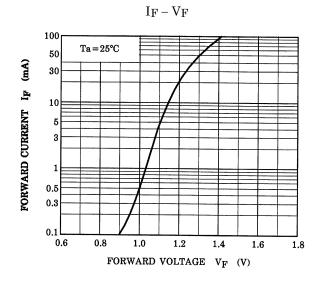
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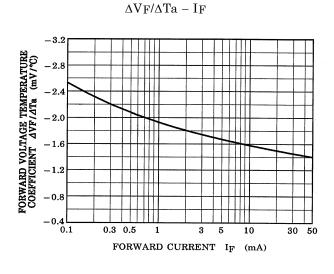
^{*:} In the case of TLP3022

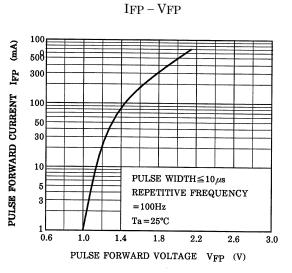




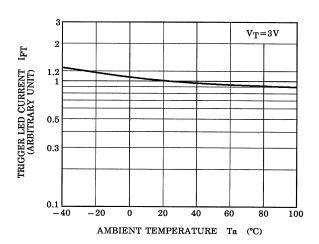




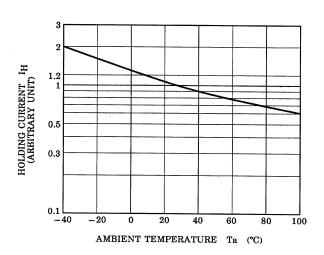




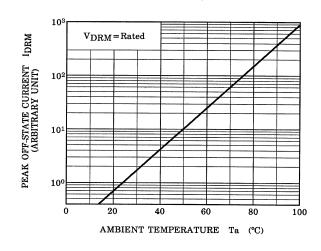
 $NORMALIZED I_{FT} - Ta$



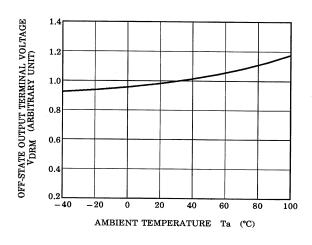
NORMALIZED I_H – Ta



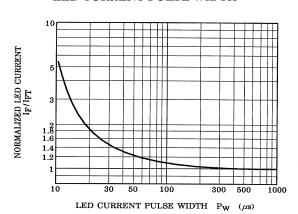
NORMALIZED IDRM - Ta



NORMALIZED V_{DRM} - Ta



NORMALIZED LED CURRENT – LED CURRENT PULSE WIDTH



RESTRICTIONS ON PRODUCT USE

20070701-EN

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 In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.
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